THERMAL CHARACTERISTICS

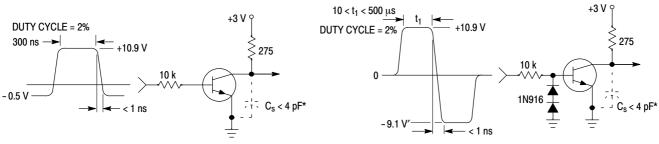
Characteristic (One Junction Heated)	Symbol	Мах	Unit	
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C (Note 1)	PD	357 2.9	mW mW/°C	
Thermal Resistance Junction-to-Ambient (Note 1)	R _{0JA}	350	°C/W	
Characteristic (Both Junctions Heated)	Symbol	Max	Unit	
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$ (Note 1)	PD	500 4.0	mW mW/°C	
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{ hetaJA}$	250	°C/W	
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C	

1. FR-4 @ Minimum Pad

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS		•		•
Collector – Emitter Breakdown Voltage (Note 2) ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	V _{(BR)CEO}	40	-	Vdc
Collector – Base Breakdown Voltage ($I_C = 10 \ \mu Adc$, $I_E = 0$)	V _{(BR)CBO}	60	-	Vdc
Emitter – Base Breakdown Voltage (I _E = 10 μ Adc, I _C = 0)	V _{(BR)EBO}	6.0	-	Vdc
Base Cutoff Current (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)	I _{BL}	-	50	nAdc
Collector Cutoff Current (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)	I _{CEX}	-	50	nAdc
ON CHARACTERISTICS (Note 2)				
$ \begin{array}{l} \text{DC Current Gain} \\ (I_{C} = 0.1 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 1.0 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 10 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 50 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 100 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 100 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}) \end{array} $	h _{FE}	40 70 100 60 30	- - 300 - -	-
Collector – Emitter Saturation Voltage ($I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$) ($I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc}$)	V _{CE(sat)}		0.2 0.3	Vdc
Base – Emitter Saturation Voltage $(I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc})$ $(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$	V _{BE(sat)}	0.65 -	0.85 0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS		•		
Current-Gain – Bandwidth Product (I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f _T	300	-	MHz
Output Capacitance (V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	-	4.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ibo}	-	8.0	pF
Input Impedance (V _{CE} = 10 Vdc, I_C = 1.0 mAdc, f = 1.0 kHz)	h _{ie}	1.0 2.0	10 12	kΩ
Voltage Feedback Ratio (V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 1.0 kHz)	h _{re}	0.5 0.1	8.0 10	X 10-4
Small-Signal Current Gain (V _{CE} = 10 Vdc, I_C = 1.0 mAdc, f = 1.0 kHz)	h _{fe}	100 100	400 400	-
Output Admittance (V_{CE} = 10 Vdc, I_C = 1.0 mAdc, f = 1.0 kHz)	h _{oe}	1.0 3.0	40 60	μmhos
Noise Figure (V _{CE} = 5.0 Vdc, I _C = 100 μ Adc, R _S = 1.0 k Ω , f = 1.0 kHz)	NF		5.0 4.0	dB

SWITCHING CHARACTERISTICS						
Delay Time	$(V_{CC} = 3.0 \text{ Vdc}, V_{BE} = -0.5 \text{ Vdc})$	t _d	-	35		
Rise Time	$(I_{\rm C} = 10 \text{ mAdc}, I_{\rm B1} = 1.0 \text{ mAdc})$	tr	-	35		
Storage Time	$(V_{CC} = 3.0 \text{ Vdc}, I_C = 10 \text{ mAdc})$	t _s	-	200		
Fall Time	(I _{B1} = I _{B2} = 1.0 mAdc)	t _f	-	50		

2. Pulse Test: Pulse Width \leq 300 µs; Duty Cycle \leq 2.0%.



* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit

Figure 2. Storage and Fall Time Equivalent Test Circuit

ns

ns

TYPICAL TRANSIENT CHARACTERISTICS

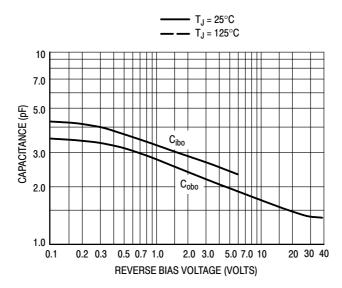
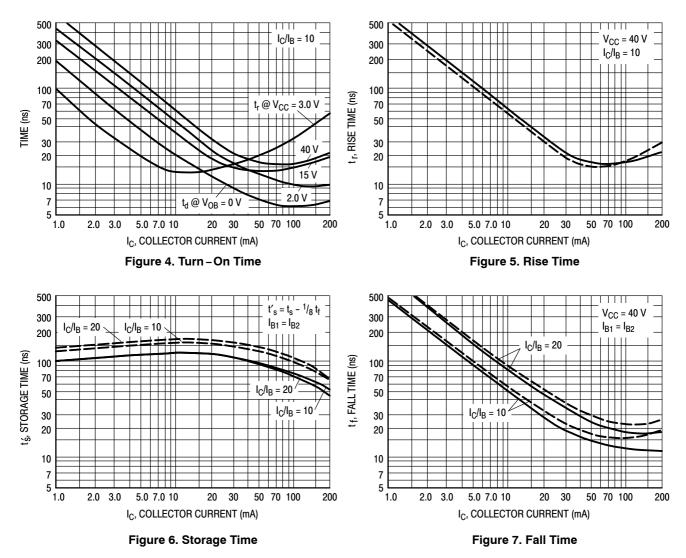


Figure 3. Capacitance



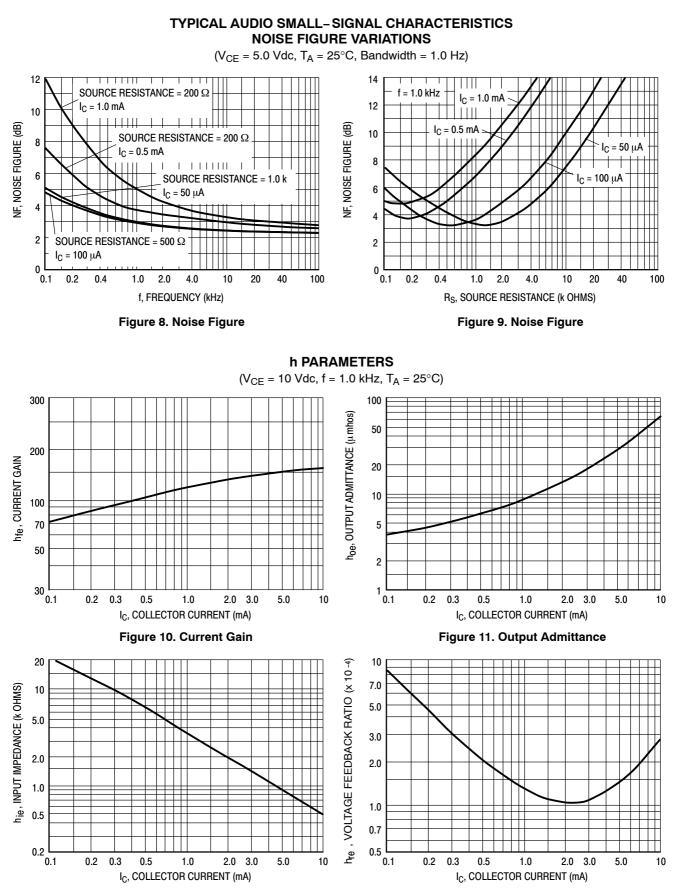
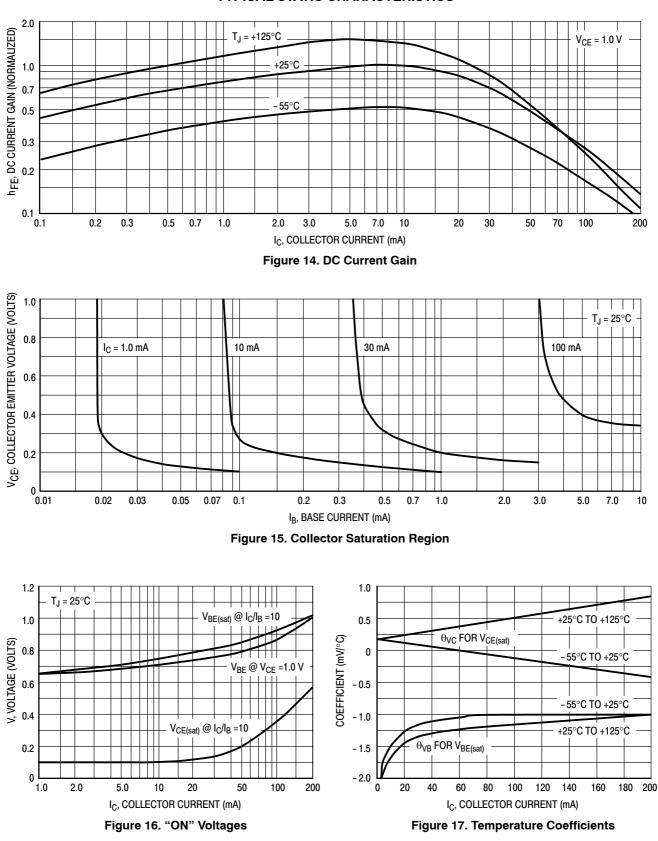


Figure 12. Input Impedance

Figure 13. Voltage Feedback Ratio



TYPICAL STATIC CHARACTERISTICS

PACKAGE DIMENSIONS

SOT-563, 6 LEAD CASE 463A-01

ISSUE F

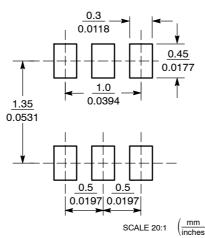
D -X-È H_{F} <u>-</u>Y 2 3 b 6 PL C е \oplus 0.08 (0.003) M X Y

NOTES 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETERS

3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.50	0.55	0.60	0.020	0.021	0.023	
b	0.17	0.22	0.27	0.007	0.009	0.011	
С	0.08	0.12	0.18	0.003	0.005	0.007	
D	1.50	1.60	1.70	0.059	0.062	0.066	
Е	1.10	1.20	1.30	0.043	0.047	0.051	
е		0.5 BSC			0.02 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012	
HE	1.50	1.60	1.70	0.059	0.062	0.066	

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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